								DITE	<u> </u>		
INFO	<b>DRM</b>	ATI	ON DISCLO	SURE	ATTY. DOCKET NO.	ATTY. DOCKET NO. SE			ERIAL NO.		
<b>1</b>					50099-238 Di		Divisi na	visi nal fAppl.N			
CITATION IN AN							09/988,59	• •			
APPLICATION							33/300,33				
(PTO-1449)					APPLICANT Shigenobu MAEDA, et al.						
										FILING DATE  December 31, 2003	FILING DATE December 31, 2003  GROUP 2823
						• ,			U.S. PATEN	T DOCUMENTS	<del></del> -
EXAMINER'S	<del></del>	Document Number Publication Date			Name of Patentee or Applicant of Cited Pages, Columns, Lines, Where						
INITIALS .	CITE NO.	Number-Kind Codez (17 known)		MM-DD-YYYY	Document		Relevant Passages or Relevant Figures Appear				
WP		US	6,410,369	06/2002	Flaker et al.	Flaker et al.					
TNP	<u> </u>	US	6,483,165	11/2002		Ooishi et al.					
WP		US	U.S.S.N. 09/466,934	12/20/1999	Yamaanahi	Yamaguchi et al.		Allowance 11/21/02			
WP	Ì	US	U.S.S.N. 09/639,953	08/17/2000	1	Iwamatin et al.		US 6,495 898			
CUP		US	U.S.S.N. 09/677,881	10/03/2000		Matsumoto et al.		US 6,455,894			
		US			7 10075 200 1000		<del>-  ```</del>	1 22 27 37, 2014			
		US				·					
		US									
		US									
	<u> </u>	US									
	<u> </u>		<u>r szészesze s</u>	<u> </u>	TENT DOCUMENTS		<del>(                                    </del>		电二级电路 医水流		
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -NumberKind Codes (# known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Where	tumns, Lines Refevant s Appear	evant			
								Yes	No		
						<u> </u>	•				
			_ · _ · _ ·								
r y hare go minorija je	22.72	13.00	2 15 HE 24 10 1 10 THE A								
EXAMINER'S	1 2 2	Llank	do some of the outbooks	CARREAL LETTERS	r, Title, Date, Pertinent Pages, E	tc.)	The second second	<u> </u>	<u> </u>		
INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.									
TWP		Hirano, et al., "Bulk-Leyout-Compatible 0.18 µm SOI-COS Technology Using Body-Fixed Partial Trench Isolation (PTI)" Proceedings of 1999 IEEE International SOI Conference, October 1999, pages, 131 – 132									
wr		ISOla	Maeda, et al., "Analysis of Delay Time Instability According to the Operating Frequency in Field Shield Isolated SOI Circuits" Proceeding of IEEE Transactions of Electron Devices, Vol. 45, No.7, July 1998, pages 1479 - 1486								
ļ	<b>-</b>	—									
<u> </u>	L	L			<del></del>						
DATE CONSIDERED  02/22/0											
EYAMINED Initial if	mhmana	coocid	and whether or not situation		''I 147-7		,				

\*EXAMIRER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.